Sentaurus Tcad User Guide

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Technology computer-aided design software (TCAD) is used to model and simulate the fabrication process (but not the behavior) of semiconductor devices. TCAD software is used to optimize semiconductor ...

Technology Computer-Aided Design Software (TCAD) Information

Top-down design approaches involve breaking down an existing product into single components. Technology computer-aided design software (TCAD) is a type of computer-aided engineering software (CAE) for ...

Computer-aided Engineering Software (CAE) Information

For many years the consensus in semiconductor chip manufacturing was that once the feature-writing capabilities of 193 nm optical lithography were exhausted, the next step would be deep-UV 157 nm ...

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Also appropriate is modeling related to the materials of interest listed below. More detailed descriptions of these areas are delineated in the Guide to Programs (NSF 97-30). It should be noted that ...

Research Topic Description

New York, US, July 01, 2021 (GLOBE NEWSWIRE) -- Market Overview: According to a comprehensive research report by Market Research Future (MRFR), 'Global ReRAM Market information by Type, by End User ...

ReRAM Market Size to Grow USD 655 Million by 2025 at a 16% CAGR - Report by Market Research Future (MRFR)

RELATED ARTICLE: TCAD software facilitates comprehensive VCSEL modeling With the addition of FEEM into DEVICE, designers are now able to analyze optical, electrical, and thermal effects within a ...

This might be the first book that deals mostly with the 3D technology computer-aided design (TCAD) simulations of major state-of-the-art stress- and strain-engineered advanced semiconductor devices: MOSFETs, BJTs, HBTs, nonclassical MOS devices, finFETs, silicon-germanium hetero-FETs, solar cells, power devices, and memory devices. The book focuses on how to set up 3D TCAD simulation tools, from mask layout to process and device simulation, including design for manufacturing (DFM), and from device modeling to SPICE parameter extraction. The book also offers an innovative and new approach to teaching the fundamentals of semiconductor process and device design using advanced TCAD simulations of various semiconductor structures. The simulation examples chosen are from the most popular devices in use today and provide useful technology and device physics insights. To extend the role of TCAD in today's advanced technology era, process compact modeling and DFM issues have been included for design‐technology interface generation. Unique in approach, this book provides an integrated view of silicon technology and beyond‐with emphasis on TCAD simulations. It is the first book to provide a web-based online laboratory for semiconductor device characterization and SPICE parameter extraction. It describes not only the manufacturing practice associated with the technologies used but also the underlying scientific basis for those technologies. Written from an engineering standpoint, this book provides the process design and simulation background needed to understand new and future technology development, process modeling, and design of nanoscale transistors. The book also advances the understanding and knowledge of modern IC design via TCAD, improves the quality in micro- and nanoelectronics R&D, and supports the training of semiconductor specialists. It is intended as a textbook or reference for graduate students in the field of semiconductor fabrication and as a reference for engineers involved in VLSI technology development who have to solve device and process problems. CAD specialists will also find this book useful since it discusses the organization of the simulation system, in addition to presenting many case studies where the user applies TCAD tools in different situations.

This book demonstrates how to use the Synopsys Sentaurus TCAD 2014 version for the design and simulation of 3D CMOS (complementary metal‐oxide‐semiconductor) semiconductor nanoelectronic devices, while also providing selected source codes (Technology Computer-Aided Design, TCAD). Instead of the built-in examples of Sentaurus TCAD 2014, the practical cases presented here, based on years of teaching and research experience, are used to interpret and analyze simulation results of the physical and electrical properties of designed 3D CMOSFET (metal‐oxide‐semiconductor field-effect transistor) nanoelectronic devices. The book also addresses in detail the fundamental theory of advanced semiconductor device design for the further simulation and analysis of electric and physical properties of semiconductor devices. The design and simulation technologies for nano-semiconductor devices explored here are more practical in nature and representative of the semiconductor industry, and as such can promote the development of pioneering semiconductor devices, semiconductor device physics, and more practically-oriented approaches to teaching and learning semiconductor engineering. The book can be used for graduate and senior undergraduate students alike, while also offering a reference guide for engineers and experts in the semiconductor industry. Readers are expected to have some preliminary knowledge of the field.

Compact Models for Integrated Circuit Design: Conventional Transistors and Beyond provides a modern treatise on compact models for circuit computer-aided design (CAD). Written by an author with more than 25 years of industry experience in semiconductor processes, devices, and circuit CAD, and more than 10 years of academic experience in teaching compact modeling courses, this first-of-its-kind book on compact SPICE models for very-large-scale-integrated (VLSI) chip design offers a balanced presentation of compact modeling crucial for addressing current modeling challenges and understanding new models for emerging devices. Starting from basic semiconductor physics and covering state-of-the-art device regimes from conventional micron to nanometer, this text: Presents industry standard models for bipolar-junction transistors (BJTs), metal-oxide-semiconductor (MOS) field-effect-transistors

(FETs), FinFETs, and tunnel field-effect transistors (TFETs), along with statistical MOS models Discusses the major issue of process variability, which severely impacts device and circuit performance in advanced technologies and requires statistical compact models Promotes further research of the evolution and development of compact models for VLSI circuit design and analysis Supplies fundamental and practical knowledge necessary for efficient integrated circuit (IC) design using nanoscale devices Includes exercise problems at the end of each chapter and extensive references at the end of the book Compact Models for Integrated Circuit Design: Conventional Transistors and Beyond is intended for senior undergraduate and graduate courses in electrical and electronics engineering as well as for researchers and practitioners working in the area of electron devices. However, even those unfamiliar with semiconductor physics gain a solid grasp of compact modeling concepts from this book.

This book deals with the subject of secondary energy spectroscopy in the scanning electron microscope (SEM). The SEM is a widely used research instrument for scientific and engineering research and its low energy scattered electrons, known as secondary electrons, are used mainly for the purpose of nanoscale topographic imaging. This book demonstrates the advantages of carrying out precision electron energy spectroscopy of its secondary electrons, in addition to them being used for imaging. The book will demonstrate how secondary electron energy spectroscopy can transform the SEM into a powerful analytical tool that can map valuable material science information to the nanoscale, superimposing it onto the instrument's normal topographic mode imaging. The book demonstrates how the SEM can then be used to quantify/identify materials, acquire bulk density of states information, capture dopant density distributions in semiconductor specimens, and map surface charge distributions.

To surmount the continuous scaling challenges of MOSFET devices, FinFETs have emerged as the real alternative for use as the next generation device for IC fabrication technology. The objective of this book is to provide the basic theory and operating principles of FinFET devices and technology, an overview of FinFET device architecture and manufacturing processes, and detailed formulation of FinFET electrostatic and dynamic device characteristics for IC design and manufacturing. Thus, this book caters to practicing engineers transitioning to FinFET technology and prepares the next generation of device engineers and academic experts on mainstream device technology at the nanometer-nodes.

This book is devoted to the latest advances in the area of electrothermal modelling of electronic components and networks. It contains eight sections by different teams of authors. These sections contain the results of: (a) electro-thermal simulations of SiC power MOSFETs using a SPICE-like simulation program; (b) modelling thermal properties of inductors taking into account the influence of the core volume on the efficiency of heat removal; (c) investigations into the problem of inserting a temperature sensor in the neighbourhood of a chip to monitor its junction temperature; (d) computations of the internal temperature of power LEDs situated in modules containing multiple-power LEDs, taking into account both self-heating in each power LED and mutual thermal couplings between each diode; (e) analyses of DC-DC converters using the electrothermal averaged model of the diode–transistor switch, including an IGBT and a rapid-switching diode; (f) electrothermal modelling of SiC power BJTs; (g) analysis of the efficiency of selected algorithms used for solving heat transfer problems at nanoscale; (h) analysis related to thermal simulation of the test structure dedicated to heat-diffusion investigation at the nanoscale.

Combining cutting-edge technologies and techniques with existing approaches, this book equips you with the tools and knowledge needed to develop new energy-efficient and environmentally friendly RFID systems. As well as covering RFID basics, a wide range of new technologies is discussed, including

biodegradable and recyclable material use, energy scavenging, passive and chipless architectures, RFID passive sensors, networked RFID and RFID sensors, organic electronic devices, textile electronics, and distributed and wide area electronics. Providing a clear description of how RFID technology can enable the evolution of the Internet of Things, the book guides you down the path to facing new challenges as we move towards ubiquitous sensing for smart environments and a networked society. This is an ideal guide for researchers in academia and industry, technical managers, and graduate students in RF and wireless communications.

This handbook introduces the basic principles and fundamentals of cyber security towards establishing an understanding of how to protect computers from hackers and adversaries. The highly informative subject matter of this handbook, includes various concepts, models, and terminologies along with examples and illustrations to demonstrate substantial technical details of the field. It motivates the readers to exercise better protection and defense mechanisms to deal with attackers and mitigate the situation. This handbook also outlines some of the exciting areas of future research where the existing approaches can be implemented. Exponential increase in the use of computers as a means of storing and retrieving security-intensive information, requires placement of adequate security measures to safeguard the entire computing and communication scenario. With the advent of Internet and its underlying technologies, information security aspects are becoming a prime concern towards protecting the networks and the cyber ecosystem from variety of threats, which is illustrated in this handbook. This handbook primarily targets professionals in security, privacy and trust to use and improve the reliability of businesses in a distributed manner, as well as computer scientists and software developers, who are seeking to carry out research and develop software in information and cyber security. Researchers and advanced-level students in computer science will also benefit from this reference.

A comprehensive one-volume reference on current JLFET methods, techniques, and research Advancements in transistor technology have driven the modern smart-device revolution—many cell phones, watches, home appliances, and numerous other devices of everyday usage now surpass the performance of the room-filling supercomputers of the past. Electronic devices are continuing to become more mobile, powerful, and versatile in this era of internet-of-things (IoT) due in large part to the scaling of metal-oxide semiconductor field-effect transistors (MOSFETs). Incessant scaling of the conventional MOSFETs to cater to consumer needs without incurring performance degradation requires costly and complex fabrication process owing to the presence of metallurgical junctions. Unlike conventional MOSFETs, junctionless field-effect transistors (JLFETs) contain no metallurgical junctions, so they are simpler to process and less costly to manufacture.JLFETs utilize a gated semiconductor film to control its resistance and the current flowing through it. Junctionless Field-Effect Transistors: Design, Modeling, and Simulation is an inclusive, one-stop referenceon the study and research on JLFETs This timely book covers the fundamental physics underlying JLFET operation, emerging architectures, modeling and simulation methods, comparative analyses of JLFET performance metrics, and several other interesting facts related to JLFETs. A calibrated simulation framework, including guidance on SentaurusTCAD software, enables researchers to investigate JLFETs, develop new architectures, and improve performance. This valuable resource: Addresses the design and architecture challenges faced by JLFET as a replacement for MOSFET Examines various approaches for analytical and compact modeling of JLFETs in circuit design and simulation Explains how to use Technology Computer-Aided Design software (TCAD) to produce numerical simulations of JLFETs Suggests research directions and potential applications of JLFETs Junctionless Field-Effect Transistors: Design, Modeling, and Simulation is an essential resource for CMOS device design researchers and advanced students in the field of physics and semiconductor devices.

Responding to recent developments and a growing VLSI circuit manufacturing market, Technology Computer Aided Design: Simulation for VLSI

MOSFET examines advanced MOSFET processes and devices through TCAD numerical simulations. The book provides a balanced summary of TCAD and MOSFET basic concepts, equations, physics, and new technologies related to TCAD and MOSFET. A firm grasp of these concepts allows for the design of better models, thus streamlining the design process, saving time and money. This book places emphasis on the importance of modeling and simulations of VLSI MOS transistors and TCAD software. Providing background concepts involved in the TCAD simulation of MOSFET devices, it presents concepts in a simplified manner, frequently using comparisons to everyday-life experiences. The book then explains concepts in depth, with required mathematics and program code. This book also details the classical semiconductor physics for understanding the principle of operations for VLSI MOS transistors, illustrates recent developments in the area of MOSFET and other electronic devices, and analyzes the evolution of the role of modeling and simulation of MOSFET. It also provides exposure to the two most commercially popular TCAD simulation tools Silvaco and Sentaurus. ▯ Emphasizes the need for TCAD simulation to be included within VLSI design flow for nano-scale integrated circuits ▯ Introduces the advantages of TCAD simulations for device and process technology characterization ▯ Presents the fundamental physics and mathematics incorporated in the TCAD tools ▯ Includes popular commercial TCAD simulation tools (Silvaco and Sentaurus) ▯ Provides characterization of performances of VLSI MOSFETs through TCAD tools ▯ Offers familiarization to compact modeling for VLSI circuit simulation R&D cost and time for electronic product development is drastically reduced by taking advantage of TCAD tools, making it indispensable for modern VLSI device technologies. They provide a means to characterize the MOS transistors and improve the VLSI circuit simulation procedure. The comprehensive information and systematic approach to design, characterization, fabrication, and computation of VLSI MOS transistor through TCAD tools presented in this book provides a thorough foundation for the development of models that simplify the design verification process and make it cost effective.